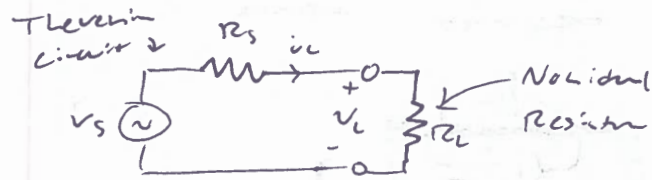


We can understand component parasitics and their effects with a simple Power Transfer Circuit



We'll take a look at

- Tolerances
- Power handling
- Parasitic capacitance

Quick Check-Your-Circuit-Knowledge: What should R_L value be (in ohms) to maximize power transfer from V_S to R_L ?

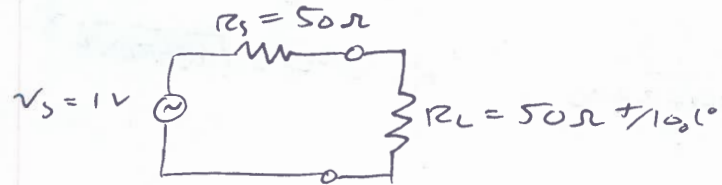
Answer: $R_S = R_L$ maximizes $\Rightarrow V_L = \frac{1}{2} V_S$, $P_L = \frac{V_S^2}{4R_L}$

Tolerances

Tolerances will typically be provided as a percentage max error that the component value can vary (1% , 5% , 10%). Typically applies to passive components like R , C , L , M .

If the value of a component is very small, often the tolerance will be provided in absolute units. Ex. a 0 ohm resistor will often have a 0.1 ohm tolerance.

Ex. Given a well matched 50 ohm system, how much power transfer degradation can we expect from a 10% resistor tolerance.



Ideal case: $P_L = \frac{1}{200}\text{ W} = 5\text{ mW}$

Worst case: $R_L = 55\text{ ohms} \rightarrow P_L = \left(\frac{R_L}{R_S + R_L} V_S \right)^2 \frac{1}{R_L}$

Difference of 0.23% $\leftarrow P_L = 4.98\text{ mW}$

$\hookrightarrow 10\%$ is fine tolerance to use

Power Handling

All Passives will have a power handling rating in some form $\rightarrow$ due to the thermal destruction of the part due to heating, especially for resistors

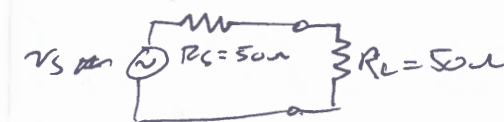
For chip resistor



Heating will cause destruction as ~~film~~ resistance film on resistor can be reduced by

- Thermally conductive substrate
- Larger device area

For 0402 part $\rightarrow P_D = 100\text{ mW}$ (loss) conduction solder connection



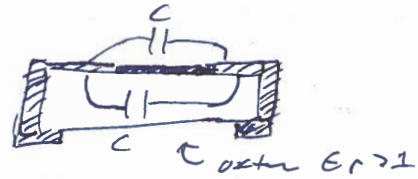
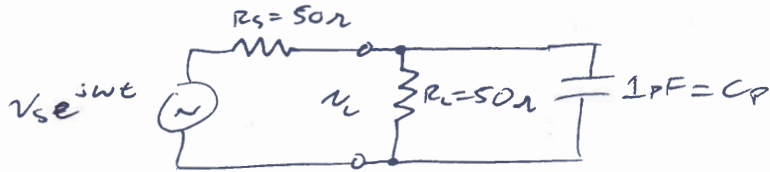
$V_S = 1\text{ V} \rightarrow P_D = 5\text{ mW}$

$V_S = 2\text{ V} \rightarrow P_D = 20\text{ mW}$

$V_S = 10\text{ V} \rightarrow P_D = 500\text{ mW} \Rightarrow$ Resistor destroyed

Parasitic Capacitance

Parasitic capacitance is often a significant limiting factor for high-frequency devices since capacitors have lower impedances as frequency increases.



$$v_L = \frac{(R_L \parallel \frac{1}{j\omega C_p})}{R_s + (R_L \parallel \frac{1}{j\omega C_p})} v_s e^{j\omega t} = \frac{(R_L / j\omega C_p) / (R_L + \frac{1}{j\omega C_p})}{R_s + (R_L / j\omega C_p) / (R_L + \frac{1}{j\omega C_p})} v_s e^{j\omega t} = \frac{(R_L / j\omega C_p)}{R_s R_L + \frac{R_s}{j\omega C_p} + \frac{R_L}{j\omega C_p}} v_s e^{j\omega t}$$

$$v_L = \frac{R_L}{R_s R_L j\omega C_p + R_s + R_L} v_s e^{j\omega t} \quad v_L = \frac{R_L}{R_s R_L j\omega C_p + R_s + R_L} v_s e^{j\omega t}$$

$$P_L = \frac{|v_L|^2}{R_L} = \frac{R_L^2}{R_L (R_s R_L j\omega C_p + R_s + R_L)^2} = \frac{R_L}{(R_s R_L j\omega C_p + R_s + R_L)^2} v_s^2$$

$$P_L = \frac{R_L^2}{(R_s R_L j\omega C_p + R_s + R_L)^2} = \frac{R_L^2}{R_s^2 R_L^2 \omega^2 C_p^2 + (R_s + R_L)^2} v_s^2$$

Now we calculate the power dissipation

$$P_L = \frac{|v_L|^2}{R_L} = \frac{v_L v_L^*}{R_L} = \frac{R_L}{R_s R_L j\omega C_p + R_s + R_L} \cdot \frac{R_L}{-R_s R_L j\omega C_p + R_s + R_L} v_s^2 = \frac{R_L^2}{R_s^2 R_L^2 \omega^2 C_p^2 + (R_s + R_L)^2} v_s^2$$

$$P_L = \frac{R_L^2 v_s^2}{R_s^2 R_L^2 \omega^2 C_p^2 + (R_s + R_L)^2}$$

We expect that $\frac{1}{2} P_{\text{max}}$ should not be dissipated by resistor at resonant frequency

$$\omega_0 = \frac{1}{RC} = \frac{1}{(R_s \parallel R_L) C_p}$$

$$\omega_0 \sim 2\pi \cdot 6 \text{ GHz}$$

therefore, use of this resonant resistor past 6 GHz is not good since much of the power will not get dissipated and will be reflected away.

Power dissipation in resistor (with parasitic parallel capacitance)

